Digital Transistors (BRT) R1 = 10 k Ω , R2 = 10 k Ω

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector–Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

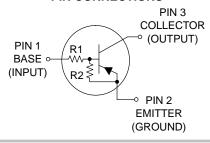
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



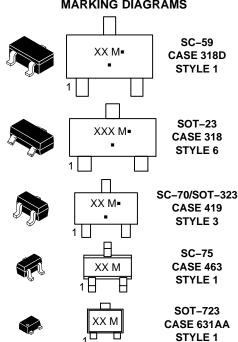
ON Semiconductor®

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PIN CONNECTIONS



MARKING DIAGRAMS



STYLE 1 XXX = Specific Device Code = Date Code* M

X ML₁

(Note: Microdot may be in either location)

= Pb-Free Package

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

SOT-1123

CASE 524AA

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2111T1G, SMUN2111T1G	6A	SC-59 (Pb-Free)	3000 / Tape & Reel
SMUN2111T3G	6A	SC-59 (Pb-Free)	10000 / Tape & Reel
MMUN2111LT1G, SMMUN2111LT1G	A6A	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMUN2111LT3G, SMMUN2111LT3G	A6A	SOT-23 (Pb-Free)	10000 / Tape & Reel
MUN5111T1G, SMUN5111T1G	6A	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA114EET1G, NSVDTA114EET1G	6A	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA114EM3T5G, NSVDTA114EM3T5G	6A	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA114EF3T5G	F	SOT-1123 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

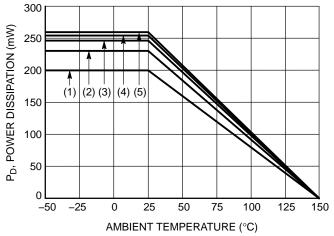


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Table 2. THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTI	CS (SC-59) (MUN2111)			
Total Device Dissipation T _A = 25°C (Note 1) (Note 2)		P _D	230 338	mW
Derate above 25°C (Note 2)	(Note 1)		1.8 2.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ heta JL}$	264 287	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SOT-23) (MMUN2111L)			
Total Device Dissipation T _A = 25°C (Note 1)		P _D	246	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		400 2.0 3.2	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SC-70/SOT-323) (MUN5111)			
Total Device Dissipation T _A = 25°C (Note 1)		P _D	202	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		310 1.6 2.5	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SC-75) (DTA114EE)			
Total Device Dissipation T _A = 25°C (Note 1)		P _D	200	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		300 1.6 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SOT-723) (DTA114EM3)			
Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1)		P _D	260	mW
(Note 2) Derate above 25°C (Note 2)	(Note 1)		600 2.0 4.8	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	480 205	°C/W
Junction and Storage Temper	ature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA114EF3)	<u>.</u>	•	
Total Device Dissipation T _A = 25°C (Note 3) (Note 4) Derate above 25°C (Note 3) (Note 4)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, (Note 3) Junction to Ambient (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead (Note 3)	$R_{ heta JL}$	193	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. FLECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	_	_	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I _{CEO}	_	_	500	nAdc
Emitter–Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	_	_	0.5	mAdc
Collector–Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _(BR) CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	_	-	Vdc
ON CHARACTERISTICS	<u>.</u>				
DC Current Gain (Note 5) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	35	60	-	
Collector–Emitter Saturation Voltage (Note 5) (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	_	_	0.25	Vdc
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μ A)	$V_{i(off)}$	_	1.2	0.8	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_{C} = 10 \text{ mA})$	V _{i(on)}	2.5	1.8	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	_	_	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R ₁ /R ₂	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS MUN2111, MMUN2111L, MUN5111, DTA114EE, DTA114EM3

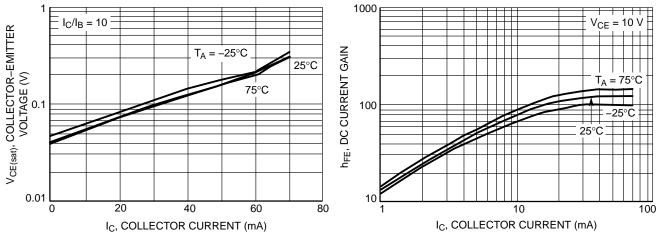


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain

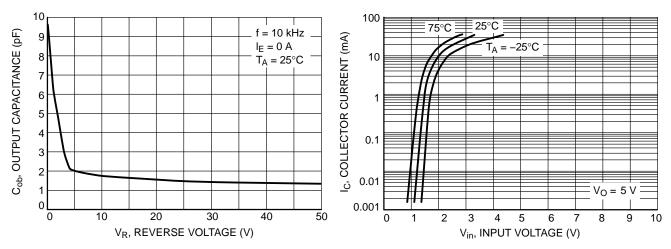


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

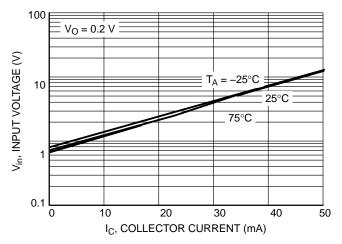
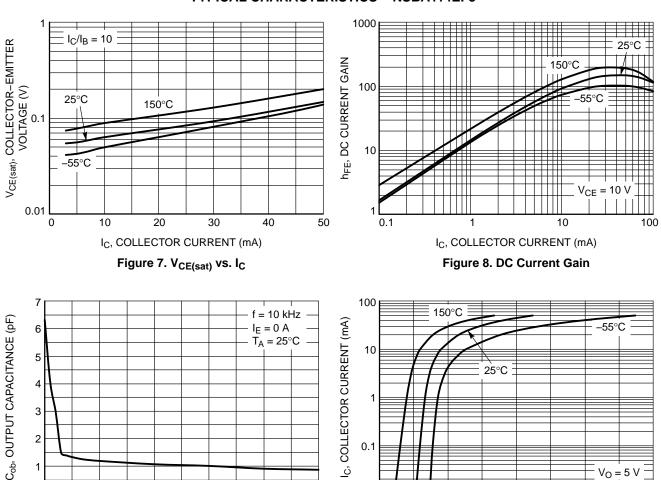


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS - NSBA114EF3



0.1

0.01

0

V_R, REVERSE VOLTAGE (V) Figure 9. Output Capacitance

20

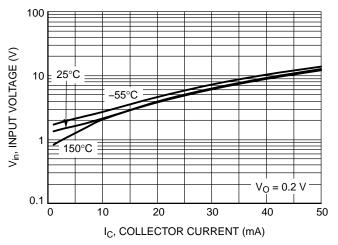
1

0

10

V_{in}, INPUT VOLTAGE (V) Figure 10. Output Current vs. Input Voltage

 $V_O = 5 V$



50

Figure 11. Input Voltage vs. Output Current





SC-70 (SOT-323) **CASE 419** ISSUE R

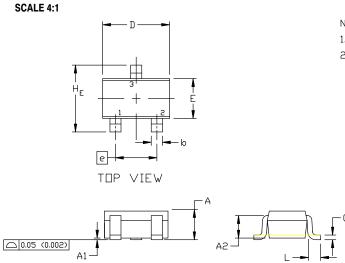
END VIEW

DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



GENERIC MARKING DIAGRAM

SIDE VIEW

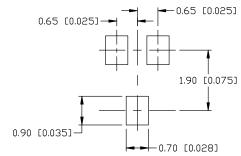


= Specific Device Code XX

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER	STYLE 7: PIN 1. BASE	STYLE 8: PIN 1. GATE	STYLE 9: PIN 1. ANODE	STYLE 10: PIN 1. CATHODE	STYLE 11: PIN 1. CATHODE
2. BASE	2. EMITTER	SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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SC75-3 1.60x0.80x0.80, 1.00P **CASE 463 ISSUE H**

DATE 01 FEB 2024

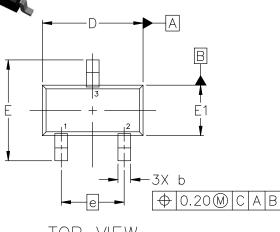
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

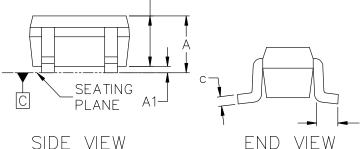
DIM	MILLIMETERS			
DIIVI	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	0.80 REF.			
Ь	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
Е	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	

-0.356

0.787



VIEW



Α2

SIDE VIEW

GENERIC MARKING DIAGRAM*



XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

1.000

RECOMMENDED MOUNTING FOOTPRINT*

1.803

0.508

STYLE 4:	STYLE 5:
PIN 1. CATHODE	PIN 1. GATE
2. CATHODE	2. SOURCE
3 ANODE	3 DRAIN

DOCUMENT NUMBER:

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DESCRIPTION: SC75-3 1.60x0.80x0.80, 1.00P

98ASB15184C

PAGE 1 OF 1

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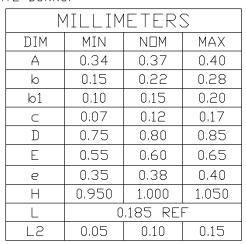


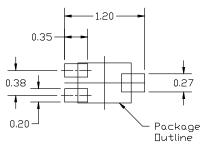
SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

DATE 18 JAN 2024

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
 OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

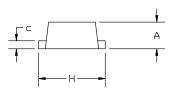




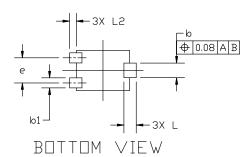
RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□LDERRM/D.

-	D	A B
		E
TOP	VIEW	



SIDE VIEW



GENERIC MARKING DIAGRAM*



X = Specific Device Code

M = Date Code

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
EMITTER	2. N/C	ANODE	CATHODE	SOURCE
COLLECTOR	CATHODE	CATHODE	3. ANODE	DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1	

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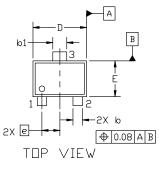


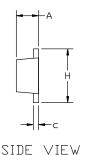
SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

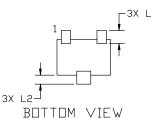
DATE 24 JAN 2024

NOTES:

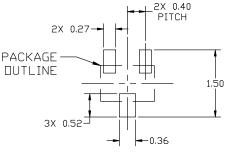
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







MILLIMETERS DIM MIN. $N\square M$. MAX. 0.45 0.50 0.55 Α 0.15 0.21 0.27 b b1 0.25 0.31 0.37 0.07 0.12 0.17 \subset D 1.25 1.15 1.20 Ε 0.75 0.80 0.85 0.40 BSC е Н 1.20 1.25 1.15 0.29 REF L L2 0.15 0.20 0.25



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	CATHODE	SOURCE
COLLECTOR	CATHODE	CATHODE	ANODE	DRAIN

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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